IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Bruce H. Baretz, et al.

in to application of Diagoni, Saioni, or an

: "SOLID STATE WHITE LIGHT EMITTER AND DISPLAY USING

SAME"

Title

U.S. Serial No.: New Continuation of Prior Copending U.S. Patent Application No.

08/621,937

Prior Application Filing Date: March 26, 1996

Prior Application Group Art Unit: 2815

Prior Application Examiner: Jerome Jackson, Jr.

"Express Mail" mailing label number: EV178871039 US

Date of Deposit: July 18, 2003

I hereby certify that this new patent application with filing fee is being deposited with the United States Postal Service "Express Mail Post Office to Addressee" service under 37 CFR 1.10 on the date indicated above and is addressed to Mail Stop BOX PATENT APPLICATION, Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450

Lee Ann DiLello

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(Signature of person mailing paper or fee)

INFORMATION DISCLOSURE STATEMENT

Commissioner for Patents P.O. Box 1450 Alexandria, VA 22313-1450

Sir:

Pursuant to 37 C.F.R. §1.56, the attention of the Patent and Trademark Office is hereby directed to the reference(s) listed on the attached PTO-1449. One copy of each reference is attached. It is respectfully requested that the information be expressly considered during the prosecution of this application, and that the reference(s) be made of record therein and appear among the "References Cited" on any patent to issue therefrom.

Docket No. ATMI-198-CON Customer ID No.: 25559

□ 1.	the U.S	formation Disclosure Statement is being filed within three months of filing date OR before the mailing date of a first Office Action on the merits. No ation or fee is required in accordance with 37 CFR § 1.56 and § 1.97(b).
□ 2.	U.S. fil	formation Disclosure Statement is being filed more than three months after the ling date AND after the mailing date of the first Office Action on the merits, but the mailing date of a Final Rejection or Notice of Allowance.
		I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of such item by a foreign patent office in a counterpart foreign application, which occurred no more than three months prior to filing the Information Disclosure Statement. 37 C.F.R. §1.97(e)(1).
		I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. §1.97(e)(2).
		Attached is our check no in the amount of \$240 in payment of the fee under 37 C.F.R. §1.17(p). Please credit or debit Deposit Account No. 50-0860 as needed to ensure consideration of the disclosed information. Two duplicate copies of this paper are attached.
□ 3.	U.S. fill but before Disclose \$130.00 Deposit	formation Disclosure Statement is being filed more than three months after the ling date and after the mailing date of a Final Rejection or Notice of Allowance, ore payment of the Issue Fee. Applicant(s) hereby petition(s) that the Information sure Statement be considered. Attached is our check no in the amount of 0 in payment of the petition fee under 37 C.F.R. §1.17(i)(1). Please credit or debit t Account No as needed to ensure consideration of the disclosed information. In plicate copies of this paper are attached.
ogovitet i		I hereby certify that each item of information contained in this Information Disclosure Statement was the first citation of such item by a foreign patent office in a counterpart foreign application which occurred no more than three months prior to filing the Information Disclosure Statement. 37 C.F.R. §1.97(e)(1).
		I hereby certify that no item of information in this Information Disclosure Statement was cited in a communication from a foreign patent office in a counterpart foreign application or, to my knowledge after making reasonable inquiry, was known to any individual designated in 37 CFR §1.56(c) more than three months prior to the filing of this Information Disclosure Statement. 37 C.F.R. §1.97(e)(2).

Docket No. ATMI-198-CON Customer ID No.: 25559

4. (other): The relevance of these references is that they were cited during the prosecution of the parent application. Copies of these references are already of record and, therefore, new copies are not being submitted along with this statement under 37 CFR 1.98(d).

Applicant does not believe that any additional fee is due in connection with the foregoing. However, any deficiencies may be charged to the deposit account 50-0860.

Respectfully submitted,

William F. Ryann

Registration No. 44,313

Attorney for Applicant

7 Commerce Drive Danbury, CT 06810

Date: July 18, 2003

Attorney Ref: ATMI-198-CON

Advanced Technology Materials, Inc.

FORM PTO-1449		US Dept. of Commerce Patent and Trademark Office		ATTORNEY DOCKET NO.		SERIAL NO.			
				ATMI-198-CON TBA					
INFORMATION DISCLOSURE STATEMENT				APPLICANT					
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(use several sheets if necessary)				FILING DATE		GROUP	GROUP		
				Herewith	TBA	TBA			
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